



BUK9Y8R7-60E,115 Information



For Reference Only

Part Number BUK9Y8R7-60E,115 **Manufacturer** Nexperia USA Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V LFPAK

Package SC-100, SOT-669

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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BUK9Y8R7-60E,115 Specifications

Manufacturer Part Number BUK9Y8R7-60E,115 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 86A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ ImA Gate Charge (Qg) (Max) @ Vgs 3lnC @ 5V Input Capacitance (Ciss) (Max) @ Vds 4570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 147W (Tc) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669		
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Package SC-100, SOT-669 Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 86A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 31nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 4570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 147W (Tc) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Manufacturer	Nexperia USA Inc.
PackageSC-100, SOT-669SeriesAutomotive, AEC-Q101, TrenchMOS?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C86A (Tc)Drive Voltage (Max Rds On, Min Rds On)5V, 10VVgs(th) (Max) @ Id2.1V @ 1mAGate Charge (Qg) (Max) @ Vgs31nC @ 5VInput Capacitance (Ciss) (Max) @ Vds4570pF @ 25VVgs (Max)±10VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs7.5 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-S08Package / CaseSC-100, SOT-669	Category	Discrete Semiconductor Products
Series Automotive, AEC-Q101, TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) four to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 86A (Tc) Drive Voltage (Max Rds On, Min Rds On) 5V, 10V Vgs(th) (Max) @ Id 2.1V @ 1mA Gate Charge (Qg) (Max) @ Vgs 31nC @ 5V Input Capacitance (Ciss) (Max) @ Vds 4570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 147W (Tc) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature 55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-S08 Package / Case SC-100, SOT-669		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C BéA (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 10V #### 10V #### 147W (Tc) Rds On (Max) @ Id, Vgs Operating Temperature - 55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case N-Camenda MOSFET (Metal Oxide) ##### MOSFET (Metal Oxide) ##### MOSFET (Metal Oxide) ###################################	Package	SC-100, SOT-669
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C B6A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case MOSFET (Metal Oxide) 80V 80V 80V 80V 80V 86A (Tc) 86A (T	Series	Automotive, AEC-Q101, TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C B6A (Tc) Prive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Togerating Temperature Poperating Temperature Power Discipation (Max) Surface Mount Supplier Device Package Package / Case SC-100, SOT-669	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature Supplier Device Package Package / Case 86A (Tc) 8	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature Surplier Device Package Package / Case SC-100, SOT-669	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 2.1V @ 1mA 2.1V @ 1mA 2.1V @ 1mA 2.1V @ 1mA 4570pF @ 25V 4	Current - Continuous Drain (Id) @ 25°C	86A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 4570pF @ 25V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Drive Voltage (Max Rds On, Min Rds On)	5V, 10V
Input Capacitance (Ciss) (Max) @ Vds 4570pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Vgs(th) (Max) @ Id	2.1V @ 1mA
Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 147W (Tc) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Gate Charge (Qg) (Max) @ Vgs	31nC @ 5V
FET Feature - 147W (Tc) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Input Capacitance (Ciss) (Max) @ Vds	4570pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7.5 mOhm @ 20A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs7.5 mOhm @ 20A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageLFPAK56, Power-SO8Package / CaseSC-100, SOT-669	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Power Dissipation (Max)	147W (Tc)
Mounting Type Surface Mount Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Rds On (Max) @ Id, Vgs	7.5 mOhm @ 20A, 10V
Supplier Device Package LFPAK56, Power-SO8 Package / Case SC-100, SOT-669	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case SC-100, SOT-669	Mounting Type	Surface Mount
	Supplier Device Package	LFPAK56, Power-SO8
Report errors?	Package / Case	SC-100, SOT-669
		Report errors?

BUK9Y8R7-60E,115 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

BUK9Y8R7-60E,115 Payment Methods



















BUK9Y8R7-60E,115 Shipping Methods













If you have any question about BUK9Y8R7-60E,115, please do not hesitate to contact us!

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